



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Kusumoto et al. Art Unit : 2814
Serial No. : 09/903,339 Examiner : Theresa T. Doan
Filed : July 10, 2001
Title : METHOD FOR PRODUCING INSULATED GATE THIN FILM
SEMICONDUCTOR DEVICE

MAIL STOP AF

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

REPLY TO ACTION OF JULY 16, 2003

TD
10/05/05
In reply to the Final Office Action of July 16, 2003, Applicants submit the following remarks.

Claims 1-30 are pending with claims 1-24 being withdrawn from consideration due to a previous restriction requirement and claims 25-30 being examined.

Claims 25-27 stand rejected under 35 U.S.C. § 102(e) as being anticipated by Zhang et al. (5,508,209). Applicants respectfully traverse this rejection.

Claim 25 recites a method of manufacturing a semiconductor device that includes, among other steps, irradiating the amorphous semiconductor film with a second harmonic of a continuous wave laser comprising Nd to crystallize the amorphous semiconductor film. Applicants request reconsideration and withdrawal of the rejection because Zhang fails to describe or suggest a method for manufacturing a semiconductor device using a second harmonic of a continuous wave laser comprising Nd. Instead, Zhang describes that a pulse laser is preferred, because a continuous oscillated laser is irradiated for an excessively long duration that can expand the object by heating and cause film peeling. After stating that a pulse laser is preferred, Zhang then proceeds to provide examples that can be used as the pulse laser. Furthermore, one of the examples that can be used as the pulse laser is a second harmonic of an infrared laser. Thus, contrary to the assertion in Office Action, Zhang (as quoted below) does not describe or suggest using a second harmonic of a continuous wave laser comprising Nd.

The laser does not need to be limited to an excimer laser, and other lasers are also usable. However, the use of a pulsed laser is preferred, because a continuous